

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)		ATTY DOCKET NO. PF-2200DIV APPLICATION NO. NEW 09/974,888 APPLICANT Yoshiaki YAMADA et al. FILING DATE October 12, 2001 GROUP UNASSIG 2823	
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U.S. PATENT DOCUMENTS									
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE			
WB	6 0 7 7 7 8 2	2000-06-01	Hsu et al.	438	688	A			
WB	6 0 5 9 8 7 2	2000-05-01	Ngan et al.	186	296-8				
WB	6 0 4 6 1 0 0	2000-04-01	Ramaswami et al.	438	624				
WB	5 9 8 5 7 5 6	1999-11-01	Shinmura	438	648	X			

FOREIGN PATENT DOCUMENTS									
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION			
						YES	NO		
WB	1 9 3 1 1 7	1989-04	JAPAN	X	X		✓		
WB	4 1 9 6 4 8 6	1992-07	JAPAN	1			✓		
WB	7 1 6 1 6 6 2	1995-06	JAPAN				✓		
WB	7 2 4 5 3 0 0	1995-09	JAPAN				✓		
WB	7 7 8 7 8 9	1995-03	JAPAN				✓		
WB	8 7 8 5 2 0	1996-03	JAPAN				✓		
WB	8 1 8 1 2 1 2	1996-07	JAPAN				✓		
WB	9 2 2 8 0 4 2	1997-09	JAPAN				✓		
WB	10 6 5 0 0 4	1998-03	JAPAN				✓		
WB	63 1 1 1 6 6 5	1988-05	JAPAN	A	X		✓		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)	
WB	J.P. Seidel, et al. "Integrated deposition of TiN barrier layers in cluster tools", Proc. of the SPIE, Vol. 1549, pp. 30-40. (abstract)
WB	H.J. Barth, et al. "TEM analysis of the spiking mechanism in Al-filled contacts", Advanced Metallization and Interconnect Systems for ULSI Applications in 1996", pp. 305-311. (abstract)
WB	D.H. Lee, et al. "Characteristics of CMOSFETs with sputter-deposited W/TiN stack gate" 1995 Symp. on VLSI Tech. Digest of tech. Papers, IEEE and JSAP pp. 119-120.
WB	S.-L. Zhang, et al. "Influence of hydrogen on chemical vapor deposited W on sputter-deposited TiN" Applied Physics Lett., Vol. 67, No. 20, pp. 2998-3000.
WB	J. van Gogh et al., "Characterization of improved TiN films by controlled divergence sputtering, pp. 310-313, ISMIC, Vol. 101, No. 92, VMIC Conference, June 9-10, 1992.
WB	A. Mouroux, et al. "Impact of rapid thermal annealing of Ti-TiN bilayers on subsequent chemical vapor deposition", Advanced Metallization for Future ULSI. Symp., pp. 365-370. (abstract)

EXAMINER William M. Brewster	DATE CONSIDERED 7 JAN 04
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.